

“The reduction of the substitutional C content in annealed Si/SiGeC superlattices studied by dark-field electron holography”. Denneulin T, Rouvière JL, Béch   A, Py M, Barnes JP, Rochat N, Hartmann JM, Cooper D, Semiconductor science and technology **26**, 1 (2011). <http://doi.org/10.1088/0268-1242/26/12/125010>